

# **60V P-CHANNEL ENHANCEMENT MODE MOSFET**

## SUMMARY

 $V_{(BR)DSS} = -60V; R_{DS(ON)} = 0.400\Omega; I_{D} = -1.1A$ 

### DESCRIPTION

This new generation of trench MOSFETs from Zetex utilizes a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

### **FEATURES**

- Low on-resistance
- Fast switching speed
- · Low threshold
- Low gate drive
- Low profile SOIC package

## **APPLICATIONS**

- DC DC converters
- Power management functions
- Relay and solenoid driving
- Motor control

### **ORDERING INFORMATION**

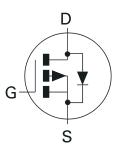
DEVICE	REEL SIZE	TAPE WIDTH	QUANTITY PER REEL
ZXMP6A13FTA	7″	8mm	3000 units
ZXMP6A13FTC	13″	8mm	10000 units

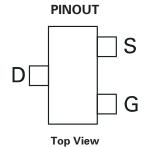
## **DEVICE MARKING**

**ISSUE 3 - MAY 2007** 

• 7P6









# ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V <sub>DSS</sub>	-60	V
Gate Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current V <sub>GS</sub> =10V; T <sub>A</sub> =25°C $^{(b)}$ V <sub>GS</sub> =10V; T <sub>A</sub> =70°C $^{(b)}$ V <sub>GS</sub> =10V; T <sub>A</sub> =25°C $^{(a)}$	ID	-1.1 -0.8 -0.9	A
Pulsed Drain Current <sup>(c)</sup>	I <sub>DM</sub>	-4.0	А
Continuous Source Current (Body Diode) <sup>(b)</sup>	I <sub>S</sub>	-1.2	А
Pulsed Source Current (Body Diode) <sup>(c)</sup>	I <sub>SM</sub>	-4.0	А
Power Dissipation at T <sub>A</sub> =25°C <sup>(a)</sup> Linear Derating Factor	P <sub>D</sub>	625 5	mW mW/°C
Power Dissipation at T <sub>A</sub> =25°C <sup>(b)</sup> Linear Derating Factor	P <sub>D</sub>	806 6.5	mW mW/°C
Operating and Storage Temperature Range	T <sub>j</sub> :T <sub>stg</sub>	-55 to +150	°C

### THERMAL RESISTANCE

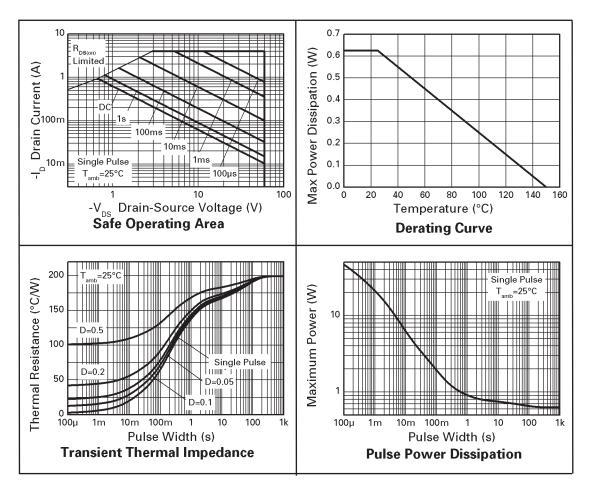
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient <sup>(a)</sup>	$R_{ extsf{ heta}JA}$	200	°C/W
Junction to Ambient <sup>(b)</sup>	$R_{\theta JA}$	155	°C/W

NOTES

(a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions (b) For a device surface mounted on FR4 PCB measured at t  $\leq$ 5 secs.

(c) Repetitive rating 25mm x 25mm FR4 PCB, D=0.05 pulse width=10µs - pulse width limited by maximum junction temperature.





## **CHARACTERISTICS**



PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS	
STATIC					1		
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	-60			V	I <sub>D</sub> =-250μA, V <sub>GS</sub> =0V	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>			-1	μA	V <sub>DS</sub> =-60V, V <sub>GS</sub> =0V	
Gate-Body Leakage	I <sub>GSS</sub>			100	nA	$V_{GS}=\pm 20V, V_{DS}=0V$	
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	-1.0			V	I <sub>D</sub> =-250μA, V <sub>DS</sub> = V <sub>GS</sub>	
Static Drain-Source On-State Resistance <sup>(1)</sup>	R <sub>DS(on)</sub>			0.400 0.600	$\Omega \\ \Omega$	V <sub>GS</sub> =-10V, I <sub>D</sub> =-0.9A V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-0.8A	
Forward Transconductance (1)(3)	9 <sub>fs</sub>		1.8		S	V <sub>DS</sub> =-15V,I <sub>D</sub> =-0.9A	
DYNAMIC <sup>(3)</sup>	•			•			
Input Capacitance	C <sub>iss</sub>		219		pF		
Output Capacitance	C <sub>oss</sub>		25.7		pF	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V, f=1MHz	
Reverse Transfer Capacitance	C <sub>rss</sub>		20.5		pF		
SWITCHING <sup>(2) (3)</sup>							
Turn-On Delay Time	t <sub>d(on)</sub>		1.6		ns		
Rise Time	t <sub>r</sub>		2.2		ns	V <sub>DD</sub> =-30V, I <sub>D</sub> =-1A R <sub>G</sub> ≅6.0Ω, V <sub>GS</sub> =-10V	
Turn-Off Delay Time	t <sub>d(off)</sub>		11.2		ns	R <sub>G</sub> ≅6.0Ω, V <sub>GS</sub> =-10V	
Fall Time	t <sub>f</sub>		5.7		ns		
Gate Charge	Qg		3.2		nC	V <sub>DS</sub> =-30V,V <sub>GS</sub> =-5V, I <sub>D</sub> =-0.9A	
Total Gate Charge	Qg		5.9		nC		
Gate-Source Charge	Q <sub>gs</sub>		0.74		nC	V <sub>DS</sub> =-30V,V <sub>GS</sub> =-10V, I <sub>D</sub> =-0.9A	
Gate-Drain Charge	Q <sub>gd</sub>		1.5		nC		
SOURCE-DRAIN DIODE						•	
Diode Forward Voltage <sup>(1)</sup>	V <sub>SD</sub>		-0.85	-0.95	V	T <sub>J</sub> =25°C, I <sub>S</sub> =-0.8A, V <sub>GS</sub> =0V	
Reverse Recovery Time <sup>(3)</sup>	t <sub>rr</sub>		21.1		ns	$T_{J}=25^{\circ}C, I_{F}=-0.9A,$	
Reverse Recovery Charge <sup>(3)</sup>	Q <sub>rr</sub>		19.3		nC	di/dt= 100A/µs	

# **ELECTRICAL CHARACTERISTICS** (at $T_A = 25^{\circ}C$ unless otherwise stated)

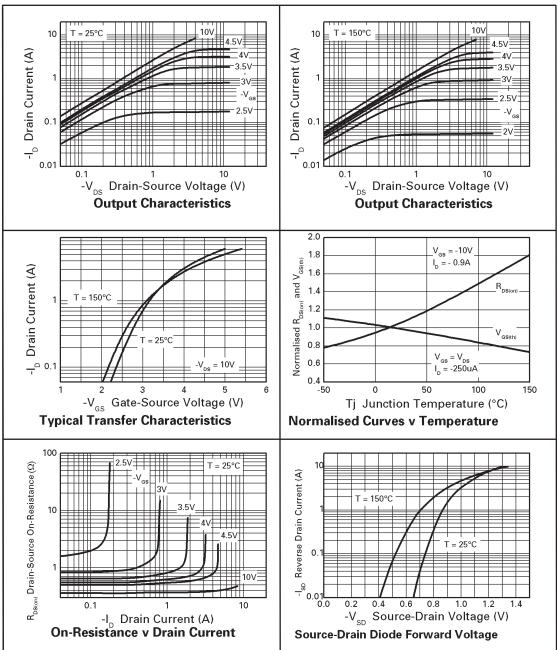
### NOTES:

(1) Measured under pulsed conditions. Width=300 $\mu s.$  Duty cycle  $\leq~2\%$  .

(2) Switching characteristics are independent of operating junction temperature.

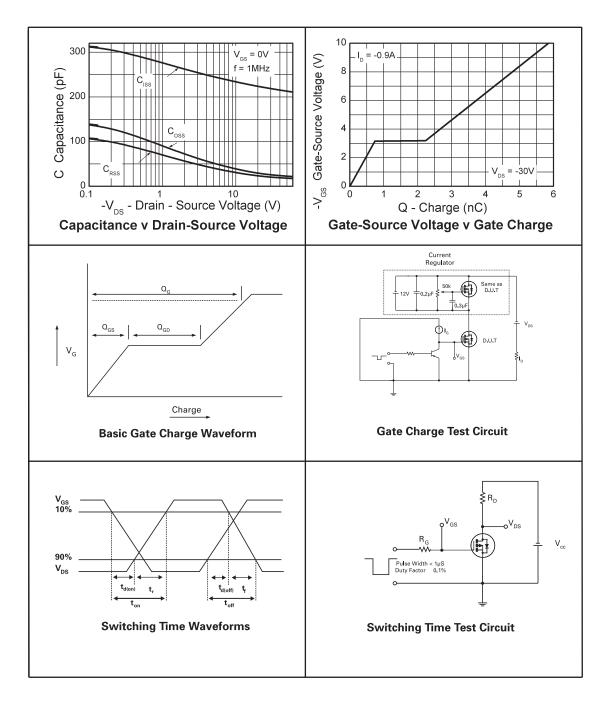
(3) For design aid only, not subject to production testing.





### **TYPICAL CHARACTERISTICS**







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"Not recommended for new designs"Device is still in production to support existing designs and production

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Datasheet status key:

"Draft version"This term denotes a very early datasheet version and contains highly provisional

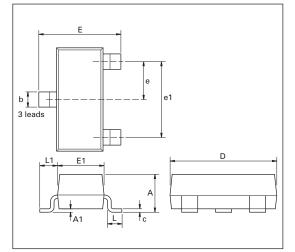
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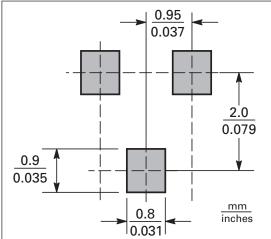
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# PACKAGE OUTLINE





PAD LAYOUT

## PACKAGE DIMENSIONS

	Millin	neters	Inc	hes		Millimeters		Inches	
DIM	Min	Max	Min	Max	DIM	Min	Max	Max	Max
А	-	1.12	-	0.044	e1	1.90	NOM	0.075	NOM
A1	0.01	0.10	0.0004	0.004	E	2.10	2.64	0.083	0.104
b	0.30	0.50	0.012	0.020	E1	1.20	1.40	0.047	0.055
С	0.085	0.20	0.003	0.008	L	0.25	0.60	0.018	0.0236
D	2.80	3.04	0.110	0.120	L1	0.45	0.62	0.018	0.024
е	0.95	NOM	0.037	NOM	—	—	_		

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